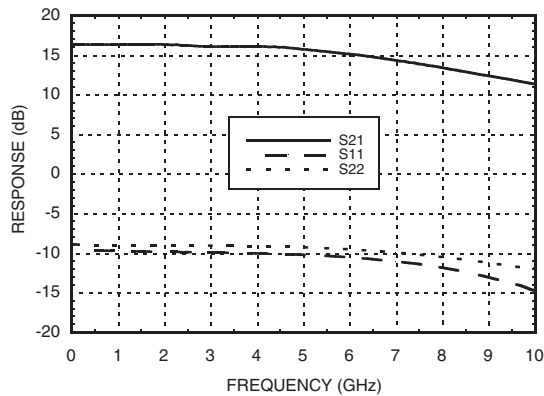
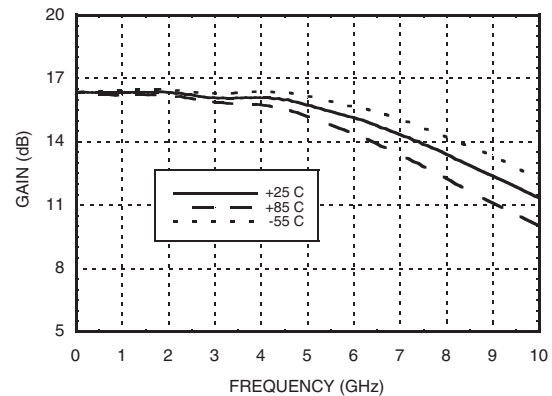


**InGaP HBT GAIN BLOCK  
MMIC AMPLIFIER, DC - 10 GHz**

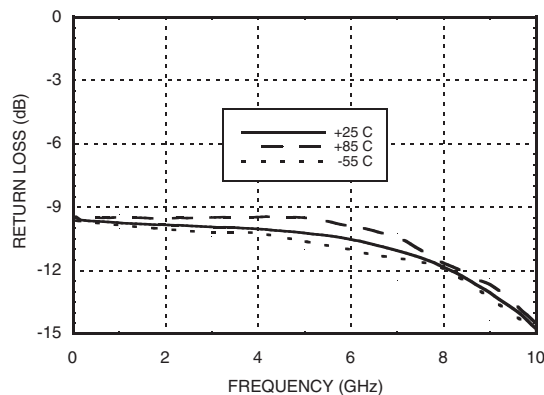
**Gain & Return Loss**



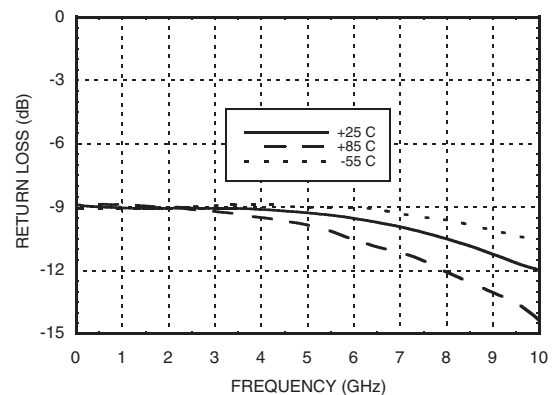
**Gain vs. Temperature**



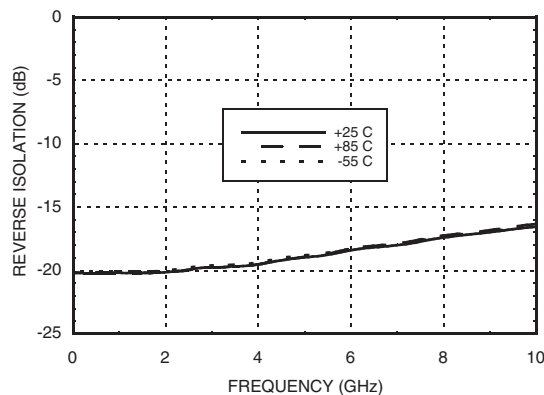
**Input Return Loss vs. Temperature**



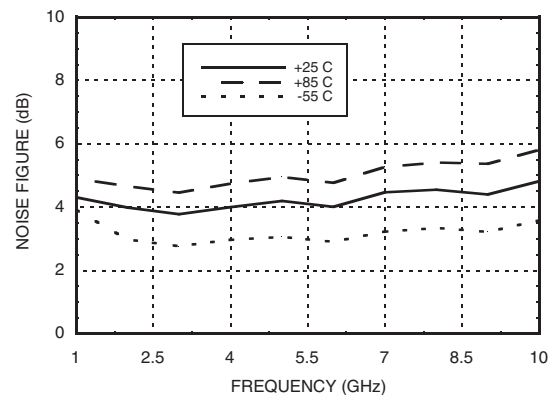
**Output Return Loss vs. Temperature**

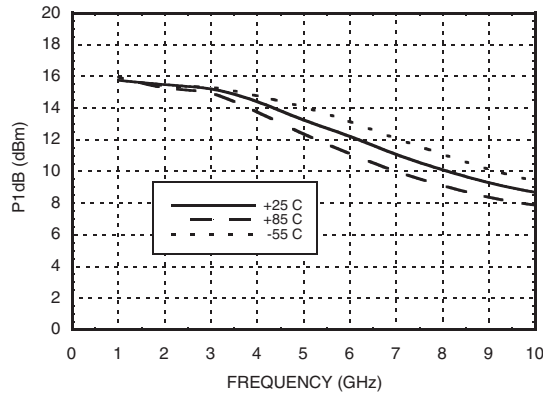
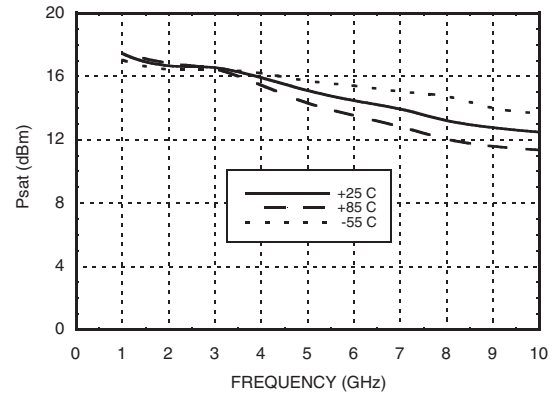
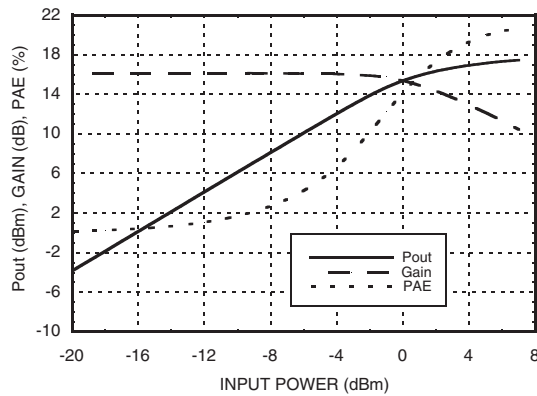
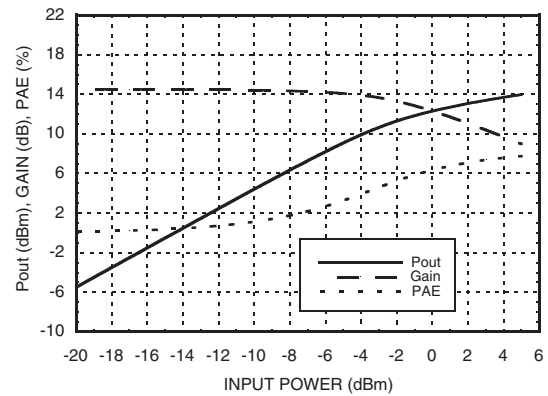
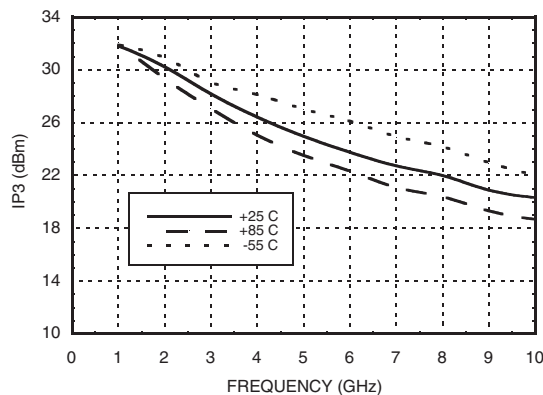
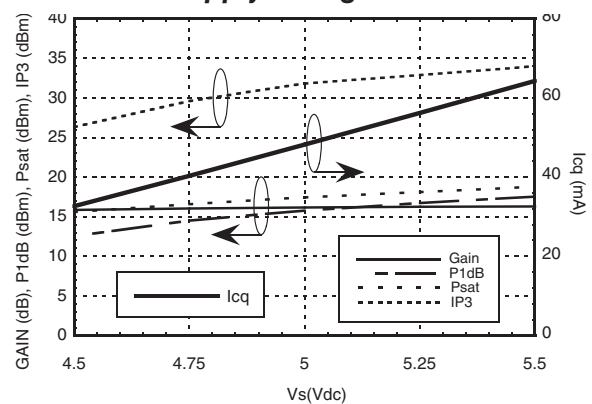


**Reverse Isolation vs. Temperature**



**Noise Figure vs. Temperature**



**InGaP HBT GAIN BLOCK  
MMIC AMPLIFIER, DC - 10 GHz**
**P1dB vs. Temperature**

**Psat vs. Temperature**

**Power Compression @ 1 GHz**

**Power Compression @ 7 GHz**

**Output IP3 vs. Temperature**

**Gain, Power, Output IP3 & Supply Current vs. Supply Voltage @ 1 GHz**


# **InGaP HBT GAIN BLOCK MMIC AMPLIFIER, DC - 10 GHz**

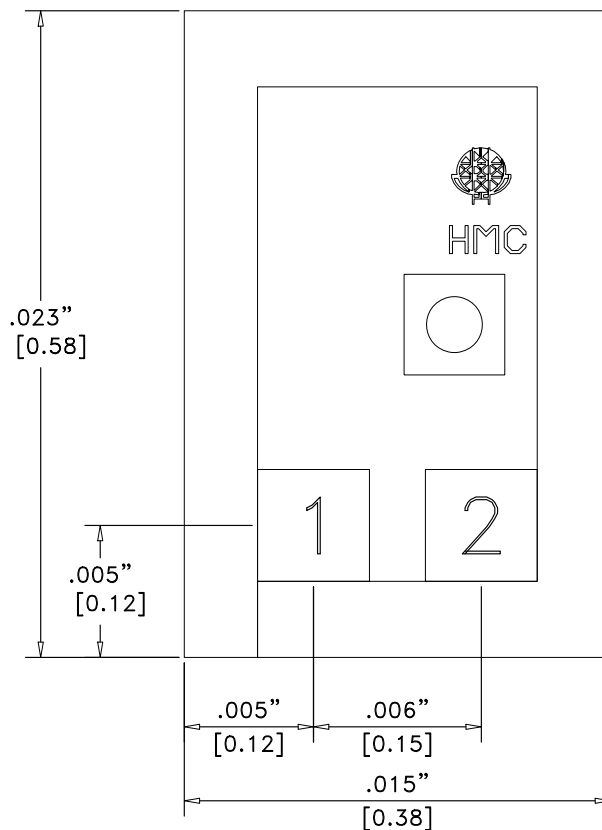
## **Absolute Maximum Ratings**

|  |                |
|--|----------------|
| Collector Bias Voltage   | +7 Vdc         |
| RF Input Power (RFiN)(Vcc = +5 Vdc)  | +10 dBm        |
| Junction Temperature   | 150 °C         |
| Continuous P <sub>diss</sub> (T= 85 °C)<br>(derate 5.21 mW/°C above 85 °C) | 0.339 W        |
| Thermal Resistance<br>(junction to die bottom)                             | 192 °C/W       |
| Storage Temperature  | -65 to +150 °C |
| Operating Temperature  | -55 to +85 °C  |



**ELECTROSTATIC SENSITIVE DEVICE  
OBSERVE HANDLING PRECAUTIONS**

## **Outline Drawing**



### **NOTES:**

1. ALL DIMENSIONS IN INCHES [MILLIMETERS]
2. ALL TOLERANCES ARE  $\pm 0.001$  (0.025)
3. DIE THICKNESS IS 0.004 (0.100) BACKSIDE IS GROUND
4. BOND PADS ARE 0.004 (0.100) SQUARE
5. BOND PAD SPACING, CTR-CTR: 0.006 (0.150)
6. BACKSIDE METALLIZATION: GOLD
7. BOND PAD METALLIZATION: GOLD

## **Die Packaging Information <sup>[1]</sup>**

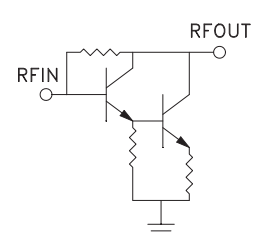

| Standard        | Alternate |
|-----------------|-----------|
| GP-3 (Gel Pack) | [2]       |

[1] Refer to the "Packaging Information" section for die packaging dimensions.

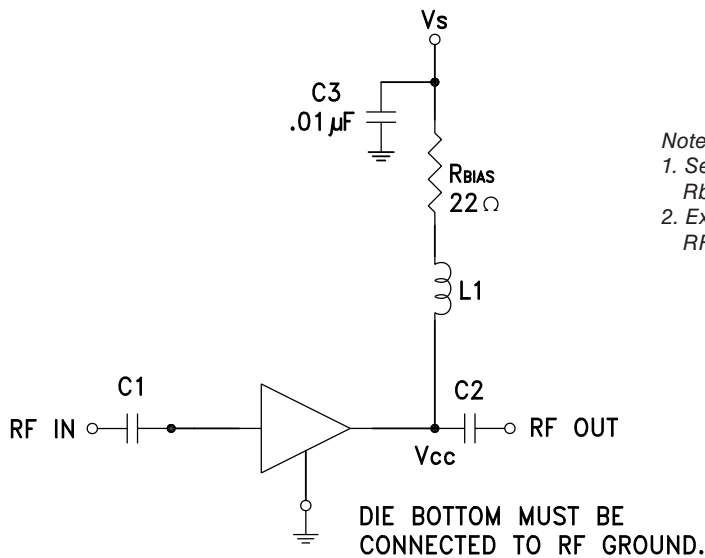
[2] For alternate packaging information contact Hittite Microwave Corporation.

# **InGaP HBT GAIN BLOCK MMIC AMPLIFIER, DC - 10 GHz**

## **Pad Descriptions**

| Pad Number | Function | Description   | Interface Schematic   |
|------------|----------|---|---|
| 1          | RFIN     | This pin is DC coupled.<br>An off chip DC blocking capacitor is required. |  |
| 2          | RFOUT    | RF output and DC Bias for the output stage.                               |   |
| Die Bottom | GND      | Die bottom must be connected to RF/DC ground.                             |  |

## **Application Circuit**



*Note:*

1. Select  $R_{bias}$  to achieve  $I_{cq}$  using equation below,  
 $R_{bias} \geq 22 \text{ Ohm}$ .
2. External blocking capacitors are required on  
 $R_{FIN}$  and  $R_{FOUT}$ .

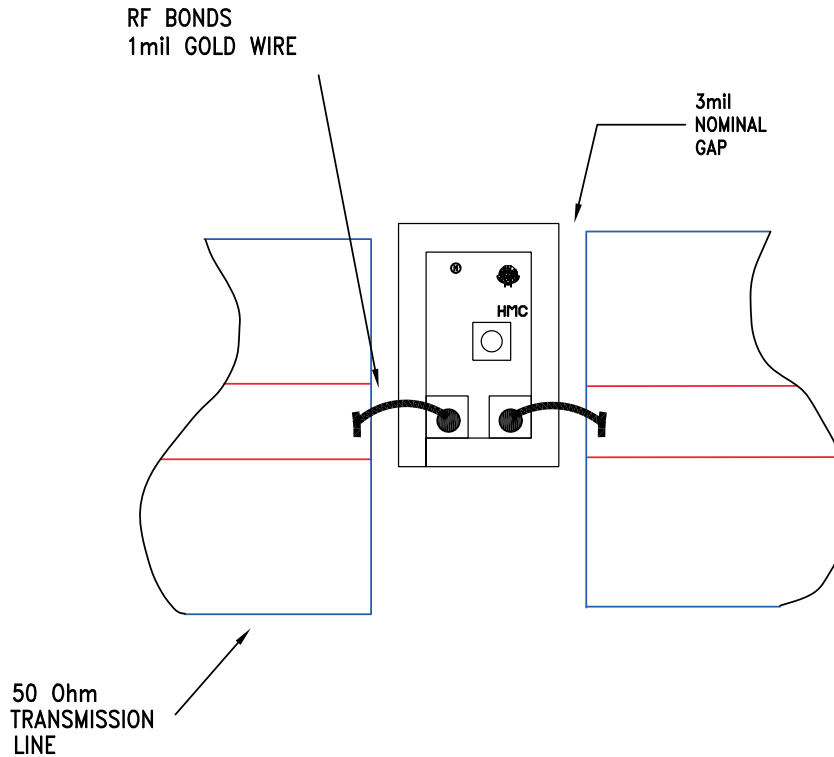
$$I_{cq} = \frac{V_s - 3.9}{R_{bias}}$$

## **Recommended Component Values**

| Component | Frequency (MHz) |        |        |        |
|-----------|-----------------|--------|--------|--------|
|           | 50              | 1000   | 3000   | 7000   |
| L1        | 270 nH          | 56 nH  | 8.2 nH | 2.2 nH |
| C1, C2    | 0.01 µF         | 100 pF | 100 pF | 100 pF |

# **InGaP HBT GAIN BLOCK MMIC AMPLIFIER, DC - 10 GHz**

## **Assembly Diagram**



## **Handling Precautions**

Follow these precautions to avoid permanent damage.

**Storage:** All bare die are placed in either Waffle or Gel based ESD protective containers, and then sealed in an ESD protective bag for shipment. Once the sealed ESD protective bag has been opened, all die should be stored in a dry nitrogen environment.

**Cleanliness:** Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.

**Static Sensitivity:** Follow ESD precautions to protect against ESD strikes.

**Transients:** Suppress instrument and bias supply transients while bias is applied. Use shielded signal and bias cables to minimize inductive pick-up.

**General Handling:** Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers. The surface of the chip has fragile air bridges and should not be touched with vacuum collet, tweezers, or fingers.

## **Mounting**

The chip is back-metallized and can be die mounted with electrically conductive epoxy. The mounting surface should be clean and flat.

**Epoxy Die Attach:** Apply a minimum amount of epoxy to the mounting surface so that a thin epoxy fillet is observed around the perimeter of the chip once it is placed into position. Cure epoxy per the manufacturer's schedule.

## **Wire Bonding**

Ball or wedge bond with 0.025mm (1 mil) diameter pure gold wire. Thermosonic wirebonding with a nominal stage temperature of 150 deg. C and a ball bonding force of 40 to 50 grams or wedge bonding force of 18 to 22 grams is recommended. Use the minimum level of ultrasonic energy to achieve reliable wirebonds. Wirebonds should be started on the chip and terminated on the package or substrate. All bonds should be as short as possible <0.31mm (12 mils).